

NB8610HD

N-Channel Power Trench MOSFET

1. FEATURES

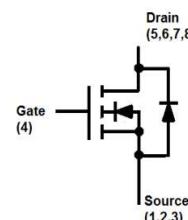
- Max RDS(on) = 13 mΩ at VGS = 10 V, ID = 8 A
- Advanced Package and Silicon combination for low RDS(on) and high efficiency.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.



DFN3333-8A

2. APPLICATIONS

- DC-DC Conversion



3. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
NB8610HD	B1H	2000/Tape&Reel

4. MAXIMUM RATINGS(Ta = 25°C unless otherwise stated)

Parameter		Symbol	Limits	Unit
Drain-to-Source Voltage		VDSS	100	V
Gate-to-Source Voltage		VGS	+20/-12	V
Avalanche Current		IAS	24	A
Avalanche energy L=0.1mH		EAS	28.8	mJ
Continuous Drain Current(Note 1)	TA =25°C	ID	14	A
	TA =70°C		9	
Pulsed Drain Current (Note 2)		IDM	56	
Continuous Source Current (Diode Conduction)(Note 1)		IS	3.5	A
Power Dissipation(Note 1)	TA =25°C	PD	3.5	W
	TA =70°C		2	
Operating Junction Temperature		TJ	-55 ~+150	°C
Storage Temperature Range		Tstg	-55 ~+150	

1.Surface Mounted on 1" x 1" FR4 Board.

2.Pulse width limited by maximum junction temperature.

5. THERMAL CHARACTERISTICS

Parameter		Symbol	Limits	Unit
Maximum Junction-to-Ambient(Note 1)	t≤10s	RθJA	35	°C/W
	Steady State		81	

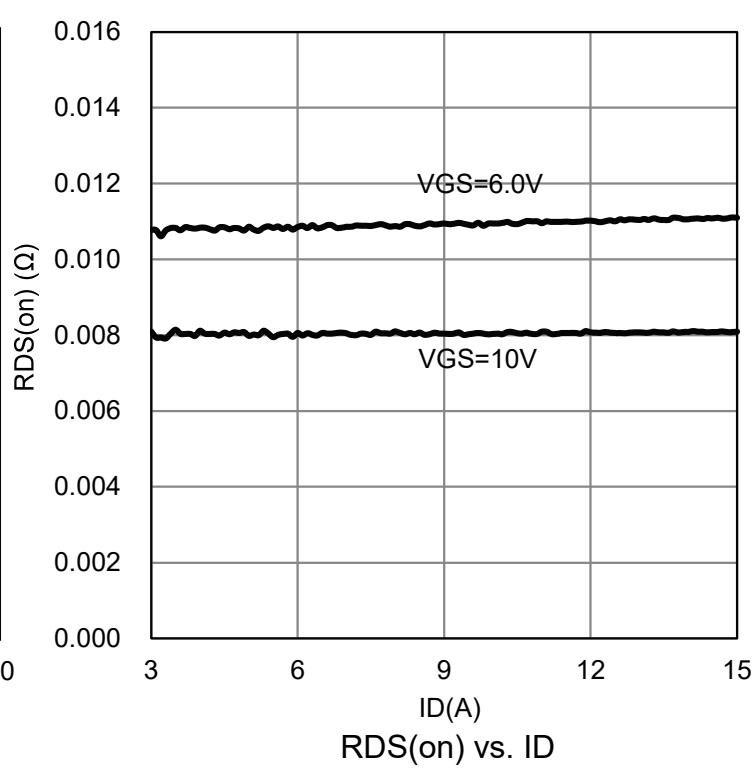
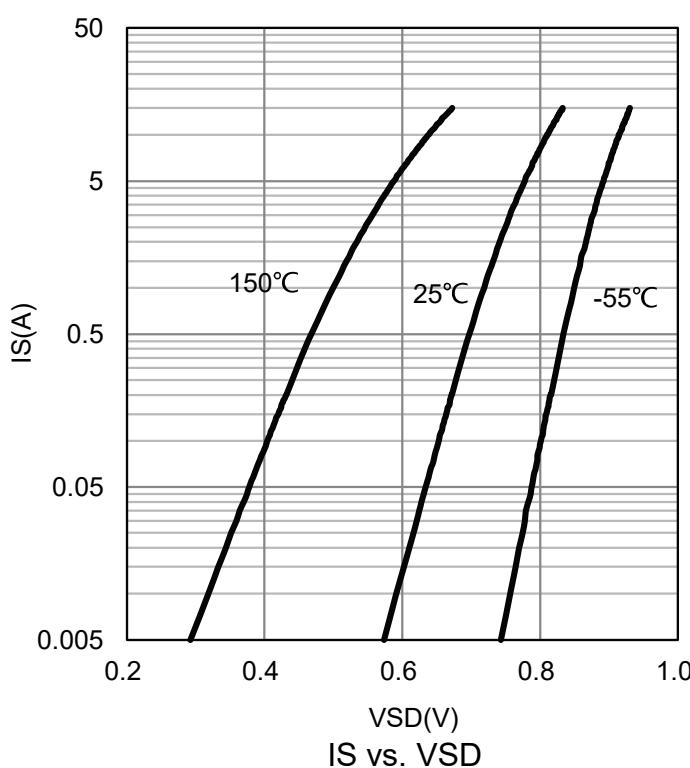
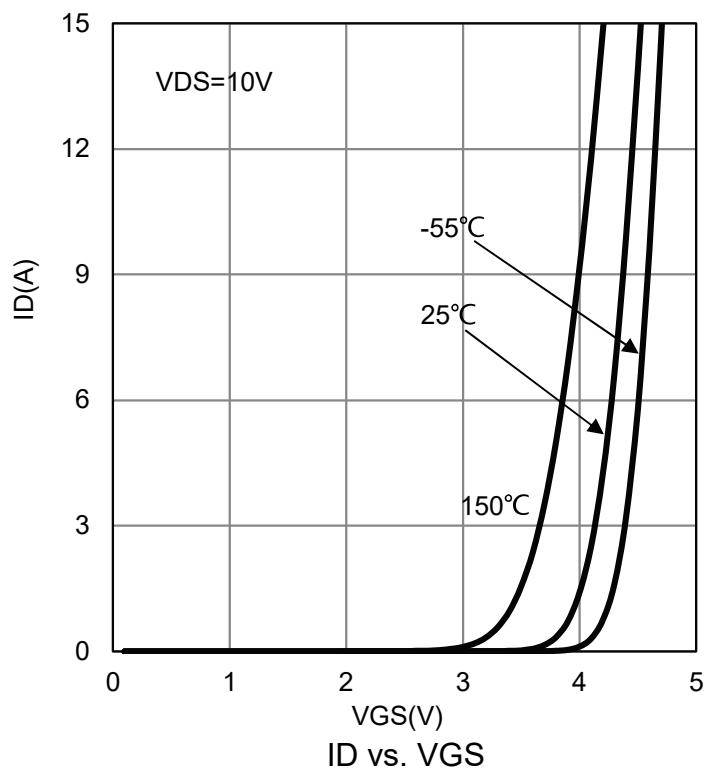
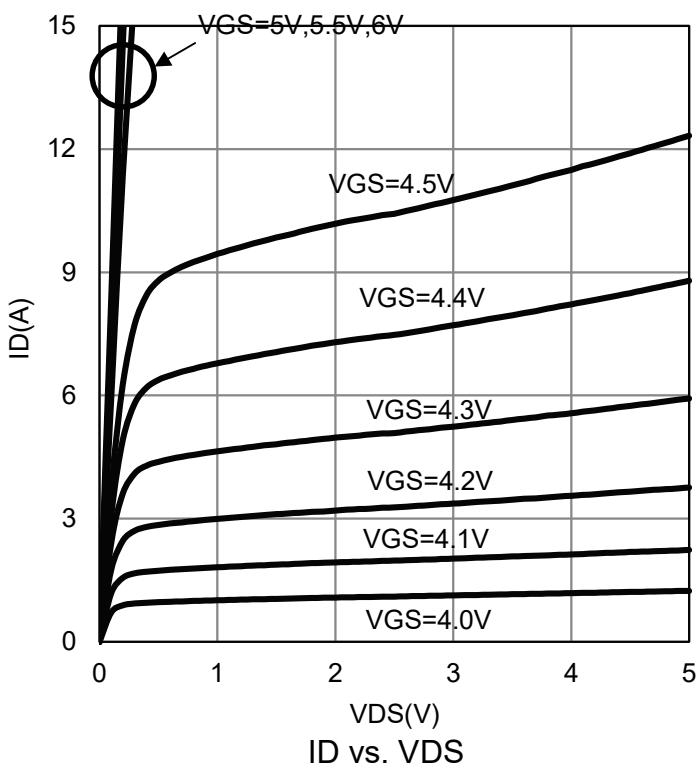


6. ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

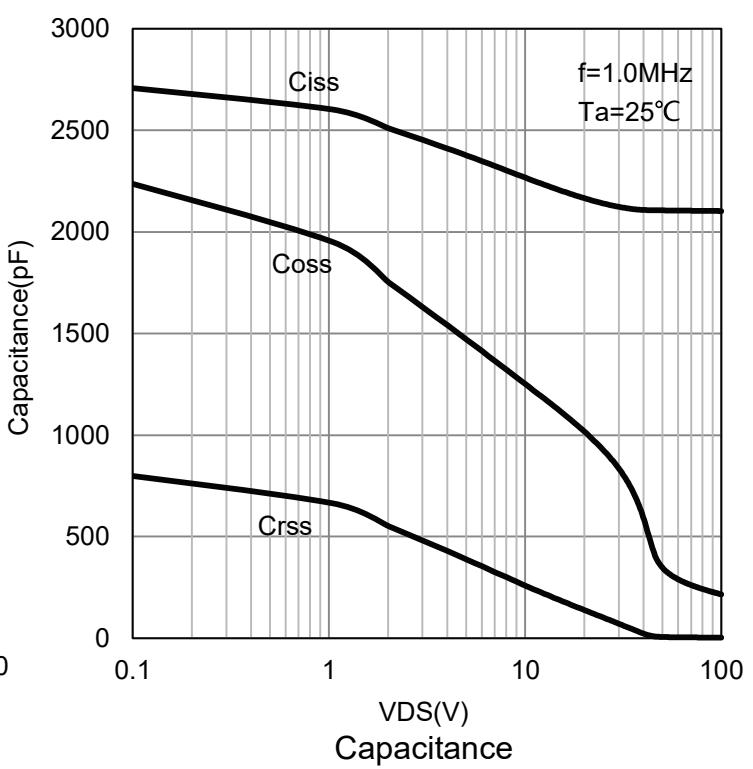
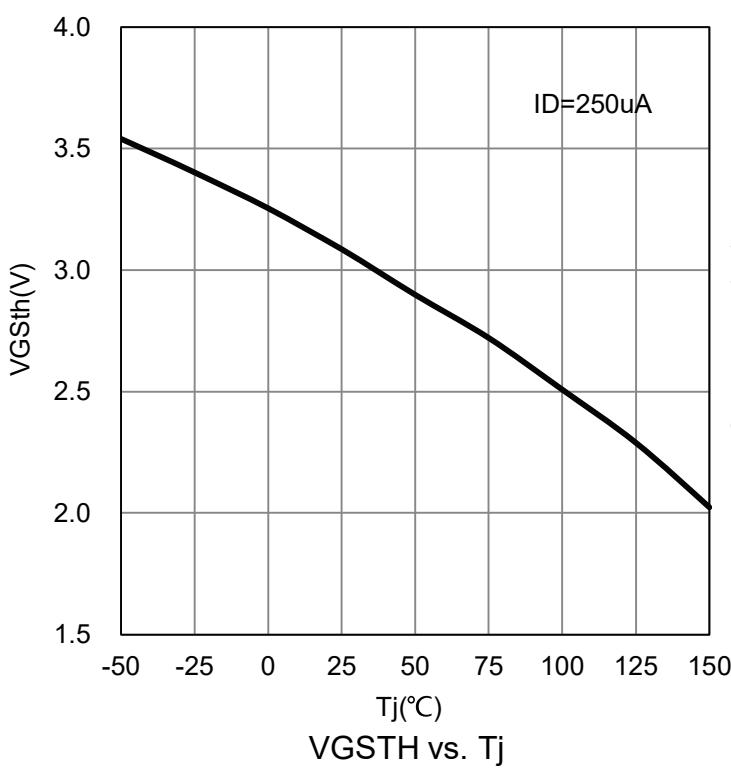
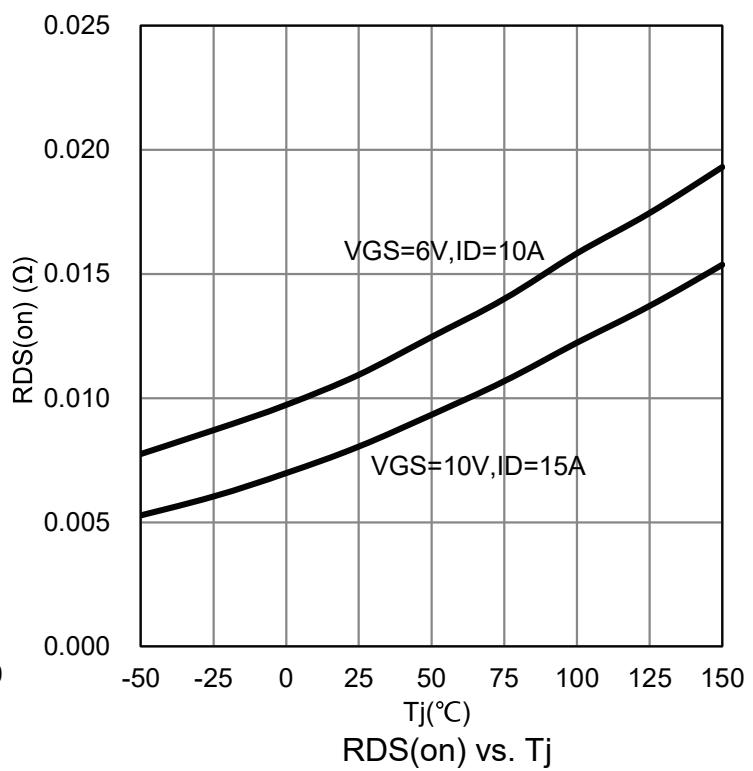
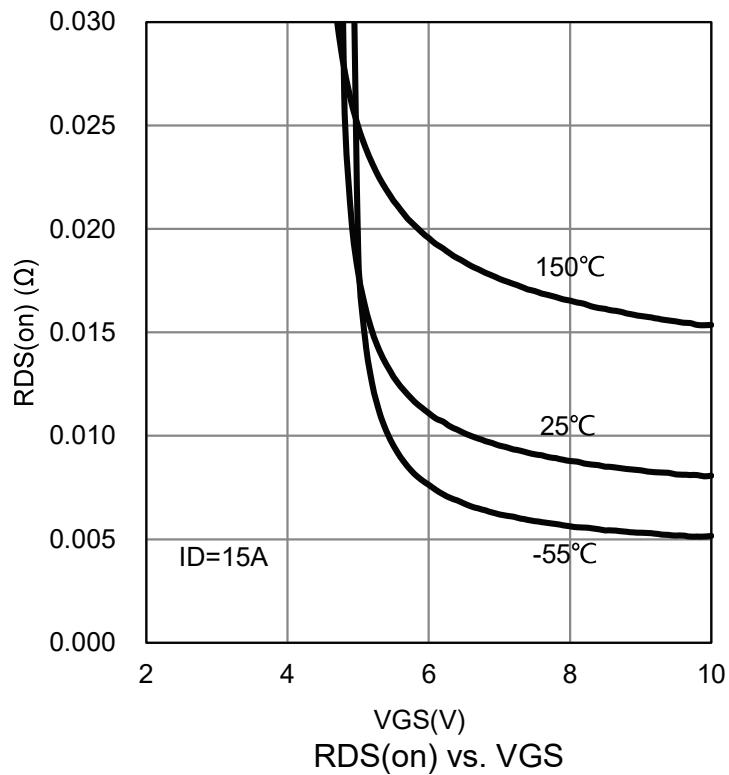
Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain to Source Breakdown Voltage ($V_{GS} = 0V$, $ID = 250\mu A$)	V_{DSS}	100	-	-	V
Drain-to-Source Leakage Current ($V_{DS} = 80V$, $V_{GS} = 0V$)	I_{DSS}	-	-	800	nA
Gate-Body leakage current ($V_{DS} = 0V$, $V_{GS} = \pm 20V$)	I_{GSS}	-	-	± 100	nA
Gate Threshold Voltage ($V_{DS} = V_{GS}$, $ID = 250\mu A$)	$V_{GS(TH)}$	2	-	4	V
Drain-to-Source On-Resistance ($V_{GS} = 10V$, $ID = 8A$) ($V_{GS} = 6V$, $ID = 5A$)	$R_{DS(ON)}$	-	9 11	13 18	$m\Omega$
Gate Resistance	R_g	-	0.6	-	Ω
Forward Transconductance ($V_{DS} = 10V$, $ID = 13A$)	g_{fs}	-	16	-	S
Total Gate Charge $V_{GS}(0 \sim 10V)$	$(ID = 13A, V_{DD} = 50V)$	Q_g	-	37	nC
Total Gate Charge $V_{GS}(0 \sim 5V)$		Q_g	-	24	
Gate to Source Charge		Q_{gs}	-	8.5	
Gate to Drain Charge		Q_{gd}	-	12	
Turn-on Delay Time	$(V_{DD} = 50V, ID = 13A, RG = 6\Omega, V_{GS} = 10V)$	$t_{d(ON)}$	-	15	nS
Rise Time		t_r	-	8	
Turn-Off Delay Time		$t_{d(OFF)}$	-	23	
Fall Time		t_f	-	7	
Input Capacitance	$(V_{GS} = 0V, V_{DS} = 50V, f = 1MHz)$	C_{iss}	-	2100	pF
Output Capacitance		C_{oss}	-	340	
Reverse Transfer Capacitance		C_{rss}	-	6.8	
Diode Forward Voltage ($V_{GS} = 0V$, $IS = 2.1A$) ($V_{GS} = 0V$, $IS = 13A$)	V_{SD}	-	0.7 0.8	1.2 1.3	V
Reverse Recovery Time ($IF = 13A$, $di/dt = 100A/\mu s$)	t_{rr}	-	56	-	nS
Reverse Recovery Charge ($IF = 13A$, $di/dt = 100A/\mu s$)	Q_{rr}	-	80	-	nC



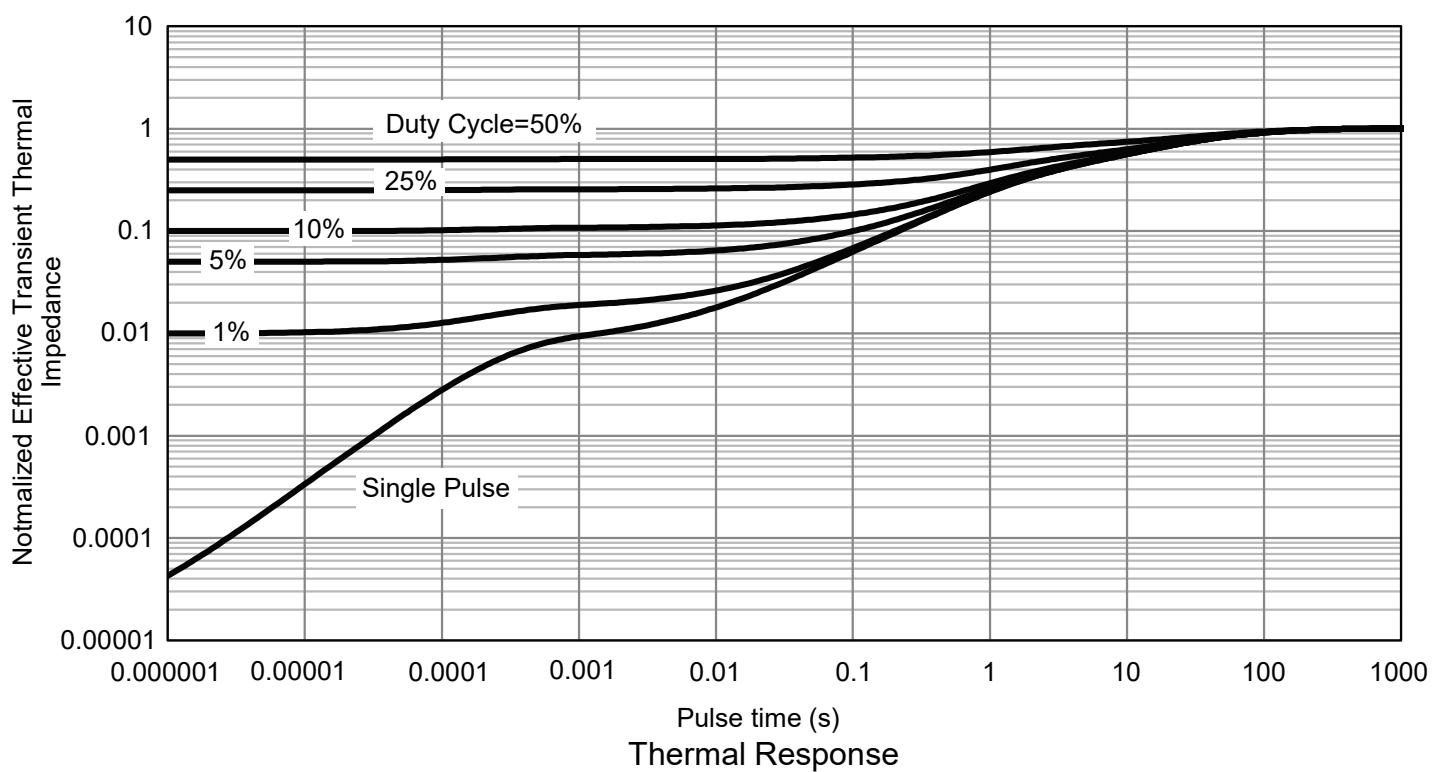
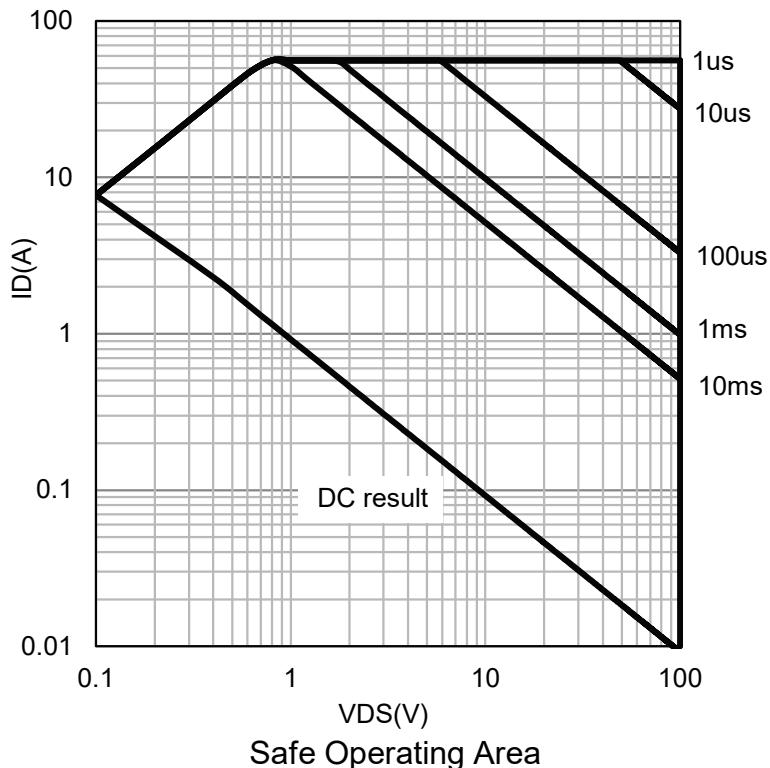
7.ELECTRICAL CHARACTERISTICS CURVES



7.ELECTRICAL CHARACTERISTICS CURVES(Con.)

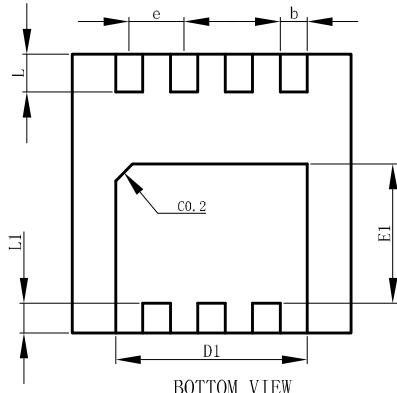
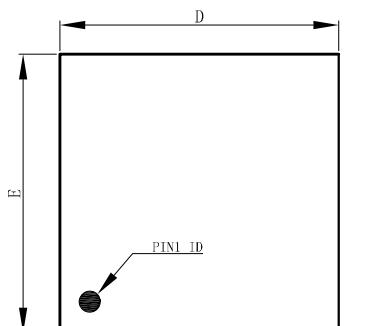


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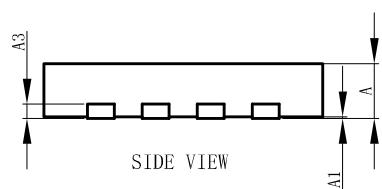


8.OUTLINE AND DIMENSIONS

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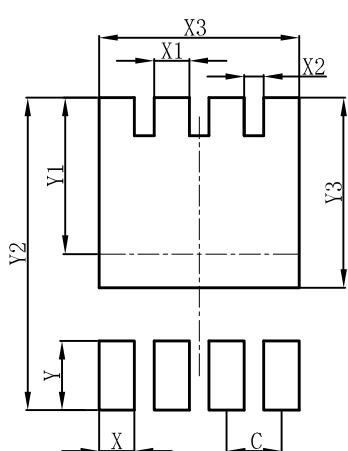


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DIM	MIN	NOR	MAX
A	0.60	0.65	0.70
A1	0.00	0.03	0.05
b	0.27	0.32	0.37
D	3.25	3.30	3.35
E	3.25	3.30	3.35
D1	2.22	2.27	2.32
E1	1.60	1.65	1.70
e	0.65BSC		
L	0.40	0.45	0.50
L1	0.30	0.35	0.40
A3	0.152REF.		
All Dimensions in mm			



9.SOLDERING FOOTPRINT

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DFN3333-8A	
DIM	(mm)
C	0.65
X	0.42
X1	0.42
X2	0.23
X3	2.37
Y	0.70
Y1	1.85
Y2	3.70
Y3	2.25

